



## Si7483ADP vs. Si7483DP

**Description:** P-Channel MOSFET

**Package:** PowerPAK® SO-8

**Pin Out:** Identical

**Part Number Replacements:**

Si7483ADP-T1 Replaces Si7483DP-T1

Lead (Pb)-free: Si7483ADP-T1-E3 Replaces Si7483DP-T1-E3

<b>ABSOLUTE MAXIMUM RATINGS</b> $T_A = 25\text{ }^\circ\text{C}$ , unless otherwise noted				
Parameter	Symbol	Si7483ADP	Si7483DP	Unit
Drain-Source Voltage	$V_{DS}$	- 30	- 30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	$\pm 20$	
Continuous Drain Current <sup>a</sup>	$T_A = 25\text{ }^\circ\text{C}$	$I_D$	- 14	A
	$T_A = 70\text{ }^\circ\text{C}$		- 11	
Pulsed Drain Current	$I_{DM}$	- 60	- 60	
Continuous Source Current <sup>a</sup> (MOSFET Diode Conduction)	$I_S$	- 1.6	- 1.6	
Power Dissipation	$T_A = 25\text{ }^\circ\text{C}$	$P_D$	1.9	W
	$T_A = 70\text{ }^\circ\text{C}$		1.2	
Operating Junction and Storage Temperature Range	$T_j$ and $T_{stg}$	- 55 to 150	- 55 to 150	$^\circ\text{C}$
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$		65	$^\circ\text{C/W}$
Maximum Junction-to-Case (Drain) <sup>a</sup>			1.5	

Notes:

a. Indicates Steady State, all others are independent of time.

b. NS denotes parameter not specified in original data sheet.

<b>SPECIFICATIONS</b> $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise noted								
Parameter	Symbol	Si7483ADP			Si7483DP			Unit
		Min	Typ	Max	Min	Typ	Max	
<b>Static</b>								
Gate-Threshold Voltage	$V_{GS(th)}$	- 1.0		- 3.0	- 1.0		- 3.0	V
Gate-Body Leakage	$I_{GSS}$			$\pm 100$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$			- 1			- 1	$\mu\text{A}$
On-State Drain Current	$V_{GS} = - 10\text{ V}$ $I_{D(on)}$	- 30			- 30			A
Drain-Source On-Resistance	$V_{GS} = - 10\text{ V}$ $r_{DS(on)}$		0.0047	0.0057		0.0041	0.005	$\Omega$
	$V_{GS} = - 4.5\text{ V}$		0.0075	0.0095		0.0077	0.0095	
Forward Transconductance	$g_{fs}$		70			70		S
Diode Forward Voltage	$V_{SD}$		- 0.73	- 1.1		- 0.75	- 1.1	V
<b>Dynamic</b>								
Total Gate Charge	$Q_g$		120	180		120	180	nC
Gate-Source Charge	$Q_{gs}$		18			18.3		
Gate-Drain Charge	$Q_{gd}$		33			33.2		
Gate Resistance	$R_g$	1.6	3.2	4.8		4		$\Omega$
<b>Switching</b>								
Turn-On Time	$t_{d(on)}$		22	35		25	40	ns
	$t_r$		33	50		40	65	
Turn-Off Time	$t_{d(off)}$		210	320		220	350	
	$t_f$		130	200		125	200	
Source-Drain Reverse Recovery Time	$t_{rr}$		70	130		87	135	

Specification comparisons are supplied as a courtesy to compare two devices and do not constitute a commercial product datasheet or any guarantee of identical performance. Designers should refer to the appropriate datasheets of the same number for guaranteed specification limits.